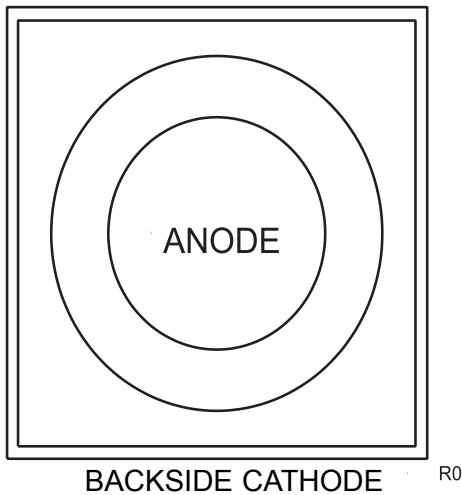


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	17.5 x 17.5 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	8.0 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

36,890

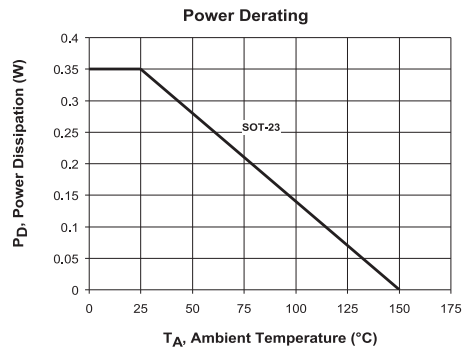
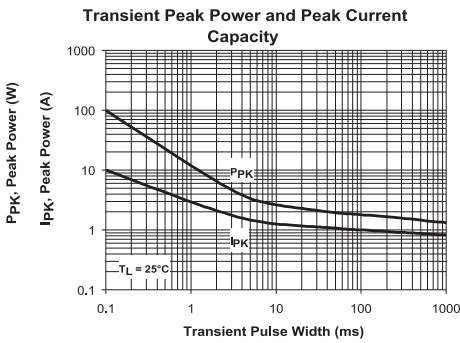
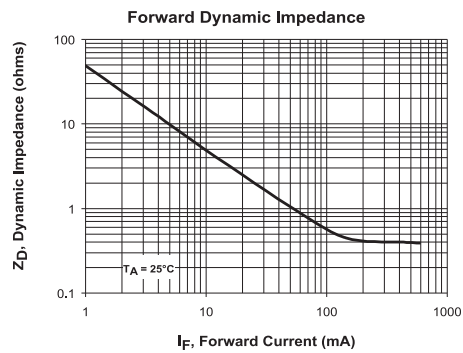
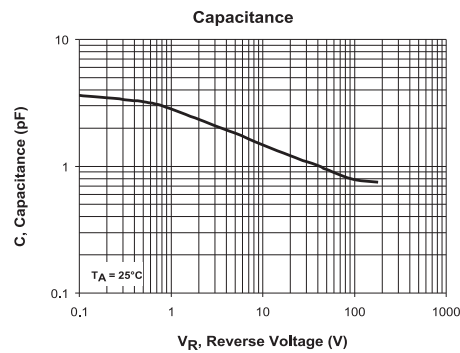
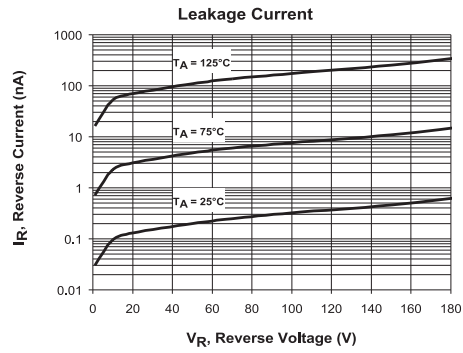
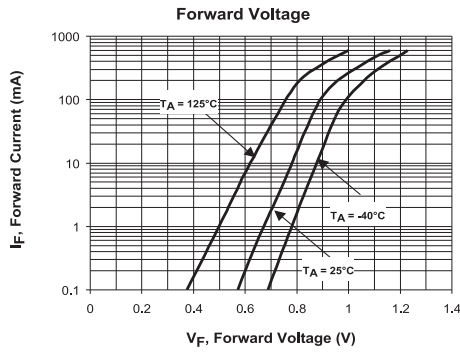
PRINCIPAL DEVICE TYPES

CMPD3003

1N3595

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